

1201.64722



PATENT APPLICATION

#161  
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6/1/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Li et al.

)  
I hereby certify that this paper is being deposited with  
the United States Postal Service as FIRST-CLASS mail  
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Patents, P.O. Box 1450, Alexandria, VA 22313-1450,  
on this date.

Serial No.: 09/662,682

)  
May 23, 2003 Ans B. R.  
Date \_\_\_\_\_  
F-CLASS.WCM \_\_\_\_\_  
Appr. February 20, 1998 \_\_\_\_\_  
Registration No. 43,874  
Attorney for Applicant

Filed: September 15, 2000

)  
For: METAL-ASSISTED CHEMICAL  
ETCH POROUS SILICON  
FORMATION METHOD

Art Unit: 1765

Examiner: Vinh, Lan

RECEIVED  
MAY 29 2003  
TC 1700

AMENDMENT D

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

In response to the Office Action mailed December 26, 2002, please  
amend the above-identified application as follows: